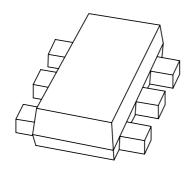
DISCRETE SEMICONDUCTORS

DATA SHEET



PEMZ7 NPN/PNP general purpose transistors

Product data sheet Supersedes data of 2001 Sep 25 2001 Nov 07



NPN/PNP general purpose transistors

PEMZ7

FEATURES

- 300 mW total power dissipation
- Very small 1.6 × 1.2 mm ultra thin package
- Self alignment during soldering due to straight leads
- Low collector capacitance
- Low V_{CEsat}
- · High current capabilities
- Improved thermal behaviour due to flat leads
- · Reduced required PCB area
- · Reduced pick and place costs.

APPLICATIONS

- Heavy duty battery powered equipment (automotive, telecom and audio-video) such as motor and lamp drivers
- V_{CEsat} critical applications such as latest low supply voltage IC applications
- All battery driven equipment, to save battery power.

DESCRIPTION

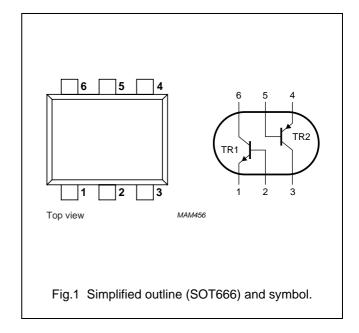
NPN/PNP low V_{CEsat} transistor pair in a SOT666 plastic package.

MARKING

TYPE NUMBER	MARKING CODE		
PEMZ7	Z7		

PINNING

PIN	DESCRIPTION		
1, 4	emitter	TR1; TR2	
2, 5	base	TR1; TR2	
6, 3	collector	TR1; TR2	



NPN/PNP general purpose transistors

PEMZ7

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT	
Per transis	Per transistor; for the PNP transistor with negative polarity					
V _{CBO}	collector-base voltage	open emitter	_	15	V	
V _{CEO}	collector-emitter voltage	open base	_	12	V	
V _{EBO}	emitter-base voltage	open collector	-	6	V	
I _C	collector current (DC)		_	500	mA	
I _{CM}	peak collector current		_	1	Α	
I _{BM}	peak base current		-	100	mA	
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	200	mW	
T _{stg}	storage temperature		-65	+150	°C	
Tj	junction temperature		_	150	°C	
T _{amb}	operating ambient temperature		-65	+150	°C	
Per device	Per device					
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	300	mW	

Note

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
R _{th j-a}	thermal resistance from junction to ambient	notes 1 and 2	416	K/W	

Notes

- 1. Transistor mounted on an FR4 printed-circuit board.
- 2. The only recommended soldering method is reflow soldering.

^{1.} Transistor mounted on an FR4 printed-circuit board.

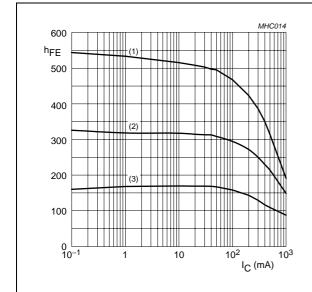
NPN/PNP general purpose transistors

PEMZ7

CHARACTERISTICS

 T_{amb} = 25 °C; unless otherwise specified.

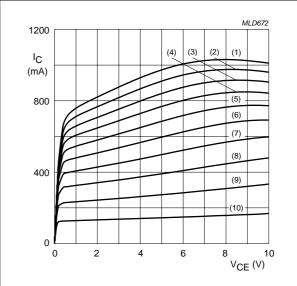
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per transis	Per transistor; for the PNP transistor with negative polarity					
I _{CBO}	collector-base cut-off current	V _{CB} = 15 V; I _E = 0	_	_	100	nA
		V _{CB} = 15 V; I _E = 0; T _j = 150 °C	_	_	50	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0	_	_	100	nA
h _{FE}	DC current gain	V _{CE} = 2 V; I _C = 10 mA	200	_	_	
V _{CEsat}	collector-emitter saturation voltage	I _C = 200 mA; I _B = 10 mA	_	-	220	mV
f _T	transition frequency TR1 (NPN)	I _C = 100 mA; V _{CE} = 5 V; f = 100 MHz	250 100	420 280	-	MHz MHz
C _c	TR2 (PNP) collector capacitance	$V_{CB} = 10 \text{ V}; I_F = I_e = 0; f = 1 \text{ MHz}$	100	200	_	IVIITZ
С	TR1 (NPN) TR2 (PNP)	VCB - 10 V, 1E - 1e - 0, 1 - 1 WII 12	_	4.4	6	pF pF



TR1 (NPN); $V_{CE} = 2 V$.

- (1) $T_{amb} = 150 \,^{\circ}\text{C}$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.2 DC current gain as a function of collector current; typical values.



TR1 (NPN); T_{amb} = 25 °C.

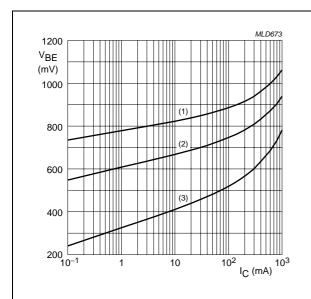
- (1) $I_B = 4.60 \text{ mA}$ (5
- (5) $I_B = 2.76 \text{ mA}$
- (9) $I_B = 0.92 \text{ mA}$
- (2) $I_B = 4.14 \text{ mA}$
- (6) $I_B = 2.30 \text{ mA}$
- (10) $I_B = 0.46 \text{ mA}$

- (3) $I_B = 3.68 \text{ mA}$
- (7) $I_B = 1.84 \text{ mA}$
- (4) $I_B = 3.22 \text{ mA}$ (8) I_B
- (8) $I_B = 1.38 \text{ mA}$

Fig.3 Collector current as a function of collector-emitter voltage; typical values.

NPN/PNP general purpose transistors

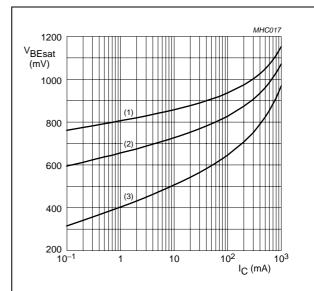
PEMZ7



TR1 (NPN); $V_{CE} = 2 V$.

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

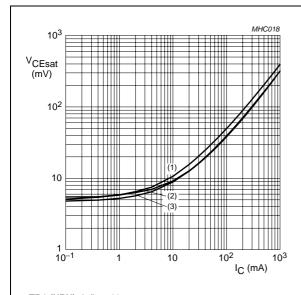
Fig.4 Base-emitter voltage as a function of collector current; typical values.



TR1 (NPN); $I_C/I_B = 20$.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

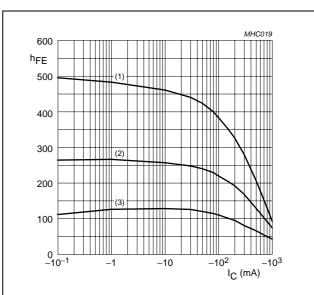
Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.



TR1 (NPN); $I_{\text{C}}/I_{\text{B}} = 20.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.6 Collector-emitter saturation voltage as a function of collector current; typical values.



TR2 (PNP); $V_{CE} = -2 \text{ V}.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.7 DC current gain as a function of collector current; typical values.

NPN/PNP general purpose transistors

PEMZ7

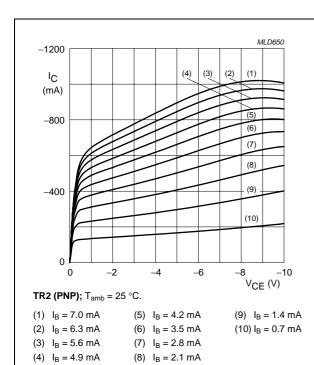
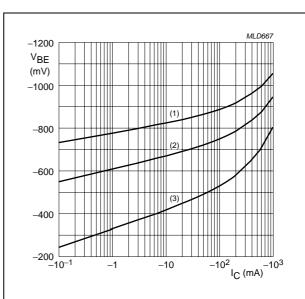


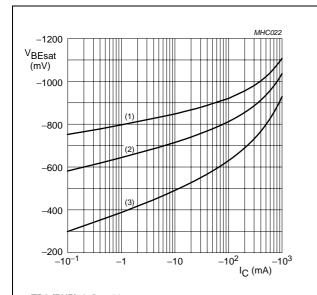
Fig.8 Collector current as a function of collector-emitter voltage; typical values.



TR2 (PNP); $V_{CE} = -2 \text{ V}$.

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

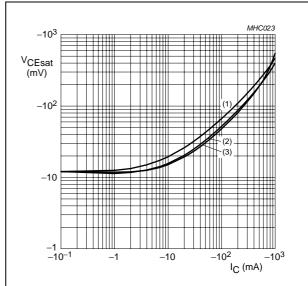
Fig.9 Base-emitter voltage as a function of collector current; typical values.



TR2 (PNP); $I_C/I_B = 20$.

- (1) T_{amb} = 150 °C.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.10 Base-emitter saturation voltage as a function of collector current; typical values.



TR2 (PNP); $I_C/I_B = 20$.

- (1) T_{amb} = 150 °C.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.11 Collector-emitter saturation voltage as a function of collector current; typical values.

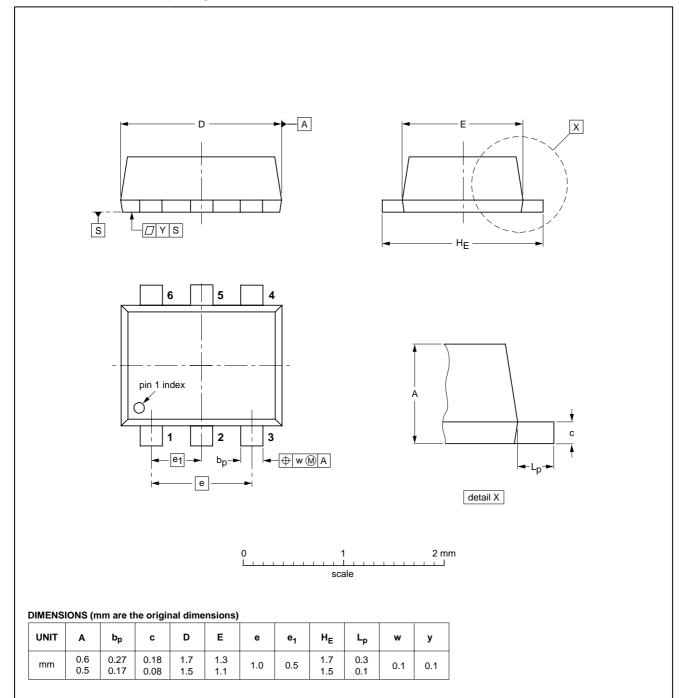
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PEMZ7

PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT666



REFERENCES

EIAJ

JEDEC

EUROPEAN

PROJECTION

ISSUE DATE

01-01-04 01-08-27

2001 Nov 07 7

IEC

OUTLINE VERSION

SOT666

NPN/PNP general purpose transistors

PEMZ7

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
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Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
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